

I. Number	Hits	Search Text	DB	Time Stamp
1	17295	floating near2 gate	USPAT; US-PGPUB; EPO; JPO	2003/06/02 17:50
2	4030	access\$3 near2 transistor	USPAT; US-PGPUB; EPO; JPO	2003/06/02 17:52
3	623025	shar\$3	USPAT; US-PGPUB; EPO; JPO	2003/06/02 17:51
4	11	common near2 region near3 storage near2 (device or cell or transistor)	USPAT; US-PGPUB; EPO; JPO	2003/06/02 17:53
5	54488	access\$3 near2 (transistor or cell or device)	USPAT; US-PGPUB; EPO; JPO	2003/06/02 17:54
7	168682	storage near2 (device or cell or transistor)	USPAT; US-PGPUB; EPO; JPO	2003/06/02 17:54
8	151	((access\$3 near2 (transistor or cell or device)) with (storage near2 (device or cell or transistor)) with shar\$3	USPAT; US-PGPUB; EPO; JPO	2003/06/02 18:09
9	0	((access\$3 near2 (transistor or cell or device)) with (storage near2 (device or cell or transistor)) with shar\$3) with drain with source	USPAT; US-PGPUB; EPO; JPO	2003/06/02 17:55
10	1001573	region	USPAT; US-PGPUB; EPO; JPO	2003/06/02 17:55
11	3	((access\$3 near2 (transistor or cell or device)) with (storage near2 (device or cell or transistor)) with shar\$3) with region	USPAT; US-PGPUB; EPO; JPO	2003/06/02 17:58
12	104300	eras\$1	USPAT; US-PGPUB; EPO; JPO	2003/06/02 17:58
13	668391	program\$4	USPAT; US-PGPUB; EPO; JPO	2003/06/02 17:58
14	11863	fowler-nordheim or fn	USPAT; US-PGPUB; EPO; JPO	2003/06/02 17:58
15	809	eras\$3 with program\$4 with (fowler-nordheim or fn)	USPAT; US-PGPUB; EPO; JPO	2003/06/02 17:59
16	502	eras\$3 near5 program\$4 near5 (fowler-nordheim or fn)	USPAT; US-PGPUB; EPO; JPO	2003/06/02 18:00
17	1085	eras\$3 near3 (fowler-nordheim or fn)	USPAT; US-PGPUB; EPO; JPO	2003/06/02 18:00
18	1	eras\$3 near3 (fowler-nordheim or fn)	USPAT; US-PGPUB; EPO; JPO	2003/06/02 18:00
19	1	eras\$3 near3 (fowler-nordheim or fn) with program\$4 near3 (fowler-nordheim or fn)	USPAT; US-PGPUB; EPO; JPO	2003/06/02 18:09
20	184	eras\$3 near5 (fowler-nordheim or fn) near5 (program\$4 near3 (fowler-nordheim or fn))	USPAT; US-PGPUB; EPO; JPO	2003/06/02 18:09
21	34086	two near2 transistor\$2	USPAT; US-PGPUB; EPO; JPO	2003/06/02 18:11
22	1	eras\$3 near3 (fowler-nordheim or fn)	USPAT; US-PGPUB; EPO; JPO	2003/06/02 18:11

25	13	"4122544" "4193080" "4258378"	USPAT	2003'06'02 18:05
26	31	"4376847" "4385308" "4462090"		
27	0	"4620361" "4639693" "4665418" "4696787").PN. 4861700.OPPN. (access\$3 near2 (transistor or cell or device)) with (storage near2 (device or cell or transistor)) with shar\$3 same (eras\$3 near3 (fowler-nordheim or fn)) near5 (program\$4 near3 (fowler-nordheim or fn))	USPAT USPAT; US-PGPUB; EPO; JPO	2003'06'02 18:06 2003'06'02 18:09
28	0	(access\$3 near2 (transistor or cell or device)) with (storage near2 (device or cell or transistor)) with shar\$3 and (eras\$3 near3 (fowler-nordheim or fn)) near5 (program\$4 near3 (fowler-nordheim or fn))	USPAT; US-PGPUB; EPO; JPO	2003 06 02 18:09
29	0	(eras\$3 near3 (fowler-nordheim or fn)) near5 (program\$4 near3 (fowler-nordheim or fn)) same (access\$3 near2 (transistor or cell or device)) same (storage near2 (device or cell or transistor))	USPAT; US-PGPUB; EPO; JPO	2003 06 02 18:11
30	12	(eras\$3 near3 (fowler-nordheim or fn)) near5 (program\$4 near3 (fowler-nordheim or fn)) and (access\$3 near2 (transistor or cell or device)) and (storage near2 (device or cell or transistor))	USPAT; US-PGPUB; EPO; JPO	2003.06.02 18:15
31	9	shallow near2 "N+" near2 source near2 region	USPAT; US-PGPUB; EPO; JPO	2003.06.02 18:16